To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

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2SK3289

Silicon N Channel MOS FET
High Speed Switching

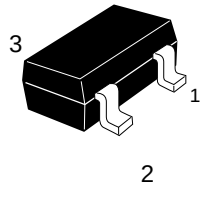
ADE-208-743B(Z)
Target Specification 3rd.Edition.
December 1998

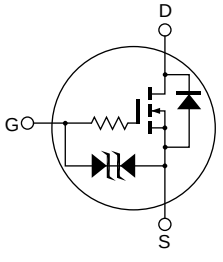
Features

- Low on-resistance
  R_{DS} = 1.26Ω typ. (at V_{GS} =10V , I_D =150mA)
  R_{DS} = 2.8Ω typ. (at V_{GS} =4V , I_D =50mA)
- 4V gate drive device
- Small package (CMPAK)

Outline

CMPAK





1. Source
2. Gate
3. Drain

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	300	mA
Drain peak current	$I_{D(pulse)}$ Note1	1.2	A
Body-drain diode reverse drain current	I_{DR}	300	mA
Channel dissipation	Pch Note 2	400	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

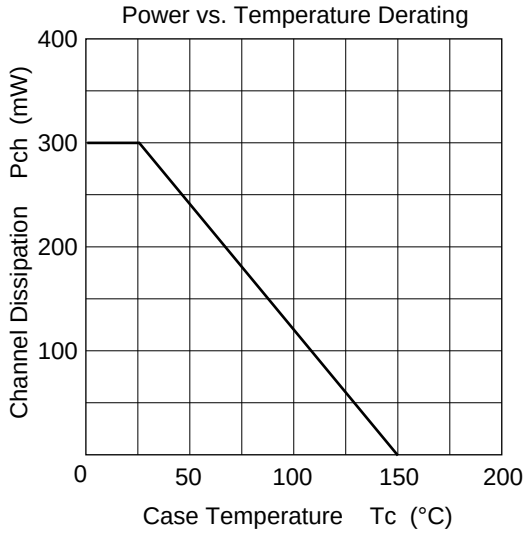
Note: 1. PW ≤ 10µs, duty cycle ≤ 1 %
2. Value on the alumina ceramic board (12.5x20x0.7mm)

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	I_D = 100µA, V_{GS} = 0
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	I_G = ±100µA, V_{DS} = 0
Gate to source leak current	I_{GSS}	—	—	±5	µA	V_{GS} = ±16V, V_{DS} = 0
Zero gate voltege drain current	I_{DSS}	—	—	1	µA	V_{DS} = 30 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	1.3	—	2.3	V	I_D = 10µA, V_{DS} = 5V
Static drain to source on state resistance	$R_{DS(on)}$	—	1.26	1.44	Ω	I_D = 150mA,V_{GS} = 10V Note 3
	$R_{DS(on)}$	—	2.8	3.44	Ω	I_D = 50mA,V_{GS} = 4V Note 3
Forward transfer admittance	$\|y_{fs}\|$	145	220	—	mS	I_D = 150mA, V_{DS} = 10V Note 3
Input capacitance	Ciss	—	4	—	pF	V_{DS} = 10V
Output capacitance	Coss	—	15	—	pF	V_{GS} = 0
Reverse transfer capacitance	Crss	—	2	—	pF	f = 1MHz
Turn-on delay time	$t_{d(on)}$	—	200	—	ns	I_D = 150mA, V_{GS} = 10V
Rise time	t_r	—	600	—	ns	R_L = 66.6Ω
Turn-off delay time	$t_{d(off)}$	—	1100	—	ns	
Fall time	t_f	—	1100	—	ns	

Note: 3. Pulse test
4. Marking is " AN "

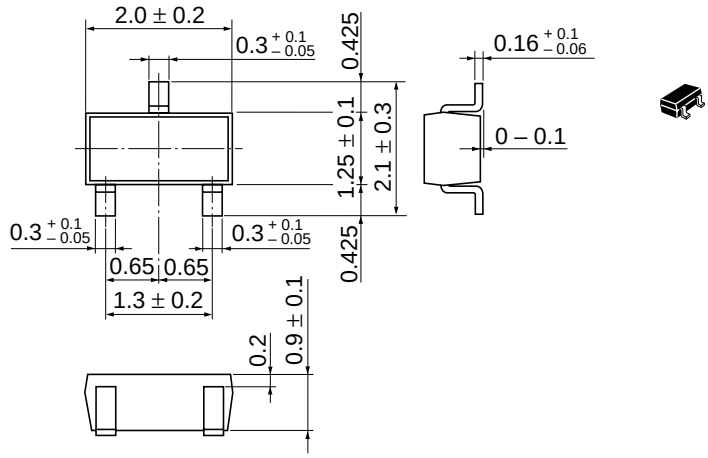
Main Characteristics



Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	CMPAK
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.006 g

Cautions

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